

High Speed IR Emitting Diode in SMD Package

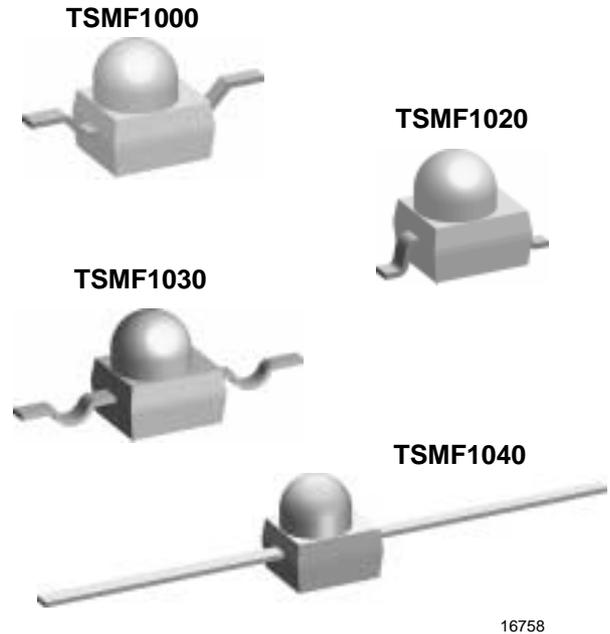
Description

TSMF1000 series are high speed infrared emitting diodes in GaAlAs/GaAs/GaAlAs double hetero technology molded in clear SMD package with dome lens.

DH chip technology represents best performance for speed, radiant power, forward voltage and longterm reliability.

Features

- High speed
- Extra high radiant power
- Low forward voltage
- Suitable for high pulse current operation
- Angle of half intensity $\phi = \pm 17^\circ$
- Peak wavelength $\lambda_p = 870 \text{ nm}$
- Longterm reliability
- Matched with PIN Photodiode TEMD1000
- Versatile terminal configurations



16758

Applications

IrDA compatible data transmission
 Miniature light barrier
 For control and drive circuits
 Photointerrupters
 Incremental sensors

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		V_R	5	V
Forward Current		I_F	100	mA
Peak Forward Current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	I_{FM}	200	mA
Surge Forward Current	$t_p = 100 \mu\text{s}$	I_{FSM}	0.8	A
Power Dissipation		P_V	190	mW
Junction Temperature		T_j	100	$^\circ\text{C}$
Operating Temperature Range		T_{amb}	-40...+85	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-40...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5\text{sec}, 2 \text{ mm from case}$	T_{sd}	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		R_{thJA}	400	K/W

Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 20\text{ mA}$	V_F		1.3	1.5	V
	$I_F = 1\text{ A}, t_p = 100\ \mu\text{s}$	V_F		2.4		V
Temp. Coefficient of V_F	$I_F = 1.0\text{ mA}$	TK_{V_F}		-1.7		mV/K
Reverse Current	$V_R = 5\text{ V}$	I_R			10	μA
Junction Capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}, E = 0$	C_j		160		pF
Radiant Intensity	$I_F = 20\text{ mA}$	I_e	2.5	5		mW/sr
	$I_F = 100\text{ mA}, t_p = 100\ \mu\text{s}$			25		
Radiant Power	$I_F = 100\text{ mA}, t_p = 20\text{ ms}$	ϕ_e		35		mW
Temp. Coefficient of ϕ_e	$I_F = 20\text{ mA}$	TK_{ϕ_e}		-0.6		%/K
Angle of Half Intensity		φ		± 17		deg
Peak Wavelength	$I_F = 20\text{ mA}$	λ_p		870		nm
Spectral Bandwidth	$I_F = 20\text{ mA}$	$\Delta\lambda$		40		nm
Temp. Coefficient of λ_p	$I_F = 20\text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise Time	$I_F = 20\text{ mA}$	t_r		30		ns
Fall Time	$I_F = 20\text{ mA}$	t_f		30		ns

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

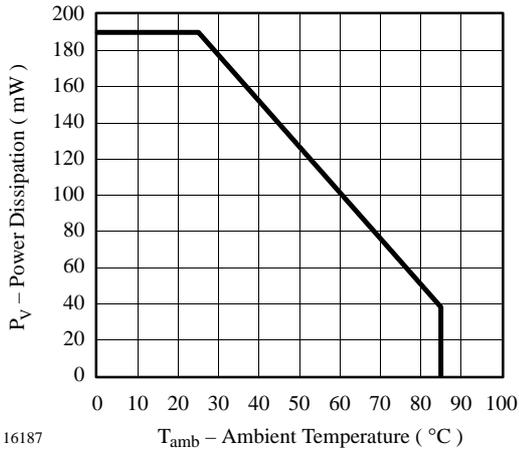


Figure 1. Power Dissipation vs. Ambient Temperature

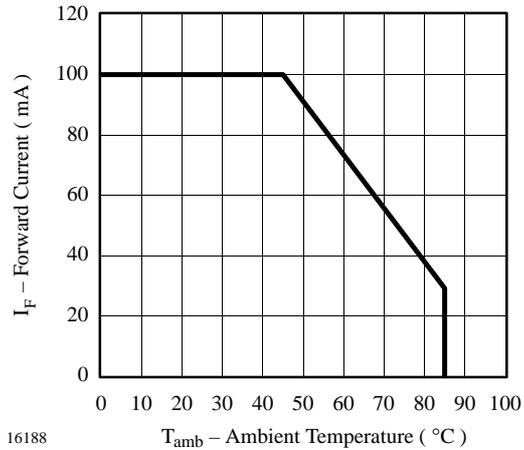
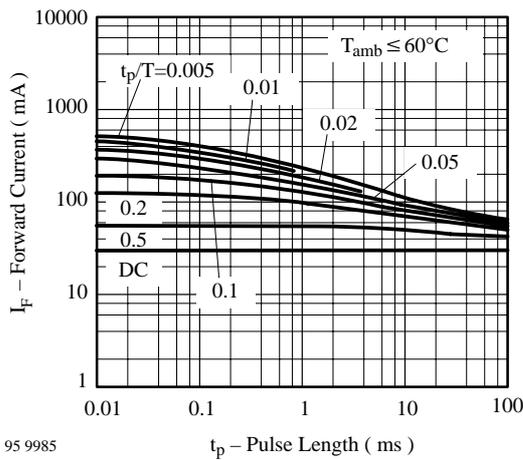
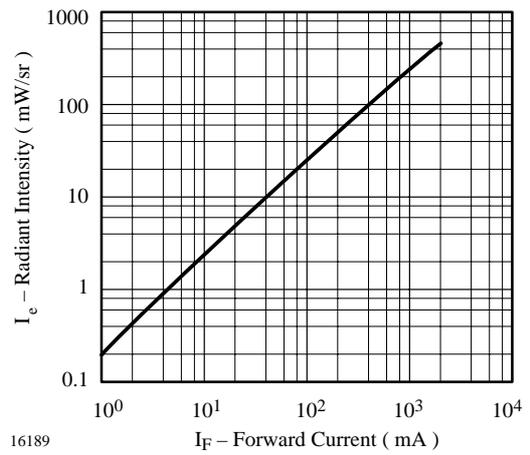


Figure 2. Forward Current vs. Ambient Temperature



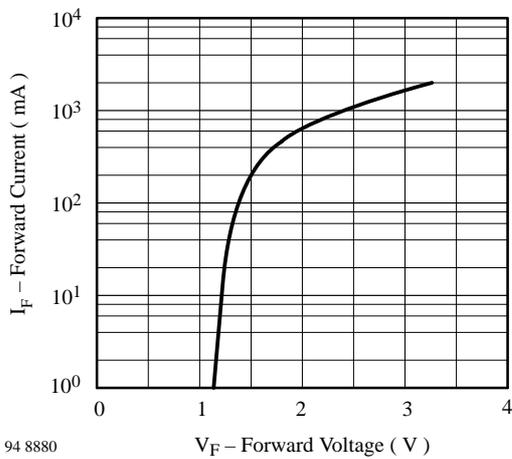
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Figure 3. Pulse Forward Current vs. Pulse Duration



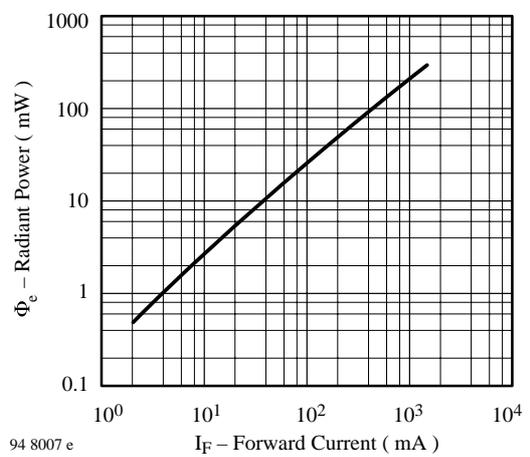
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Figure 6. Radiant Intensity vs. Forward Current



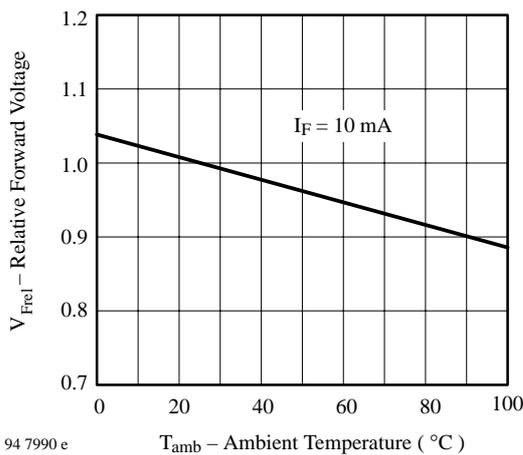
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Figure 4. Forward Current vs. Forward Voltage



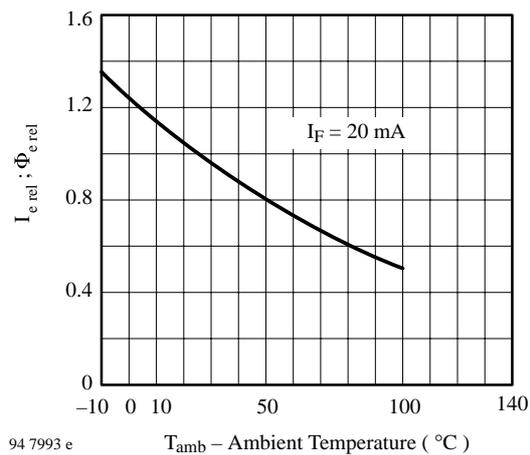
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Figure 7. Radiant Power vs. Forward Current



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Figure 5. Relative Forward Voltage vs. Ambient Temperature



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Figure 8. Rel. Radiant Intensity/Power vs. Ambient Temperature

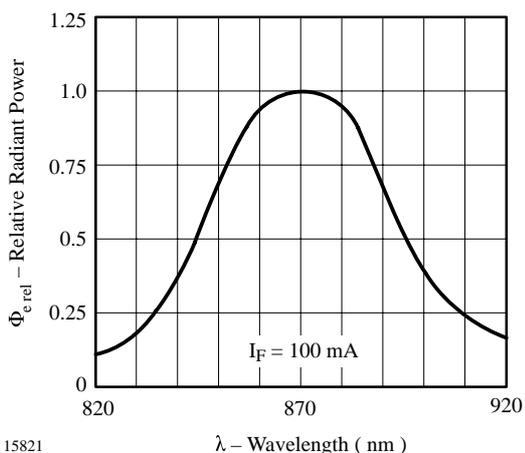


Figure 9. Relative Radiant Power vs. Wavelength

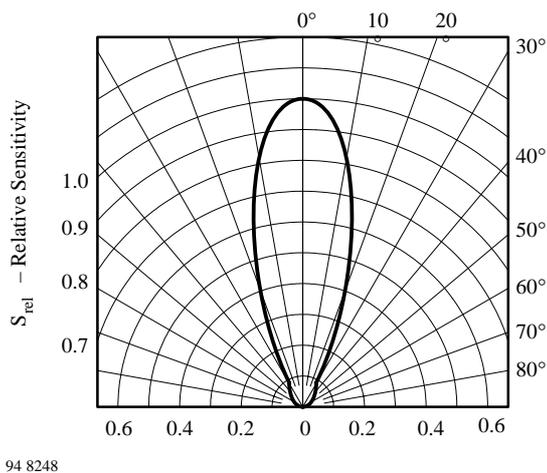
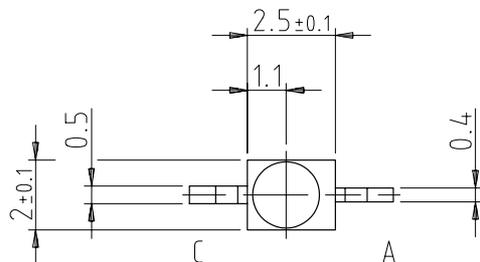
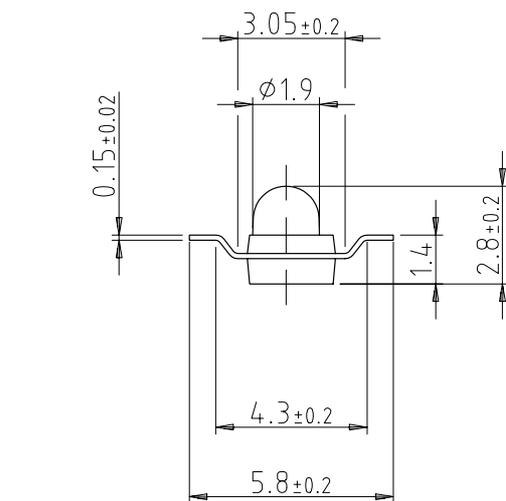
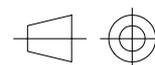


Figure 10. Relative Radiant Sensitivity vs. Angular Displacement

Dimensions in mm of TSMF1000

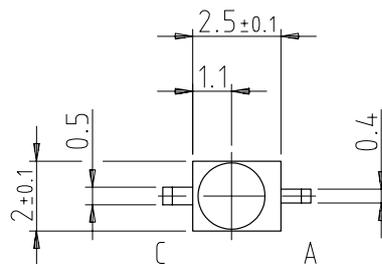
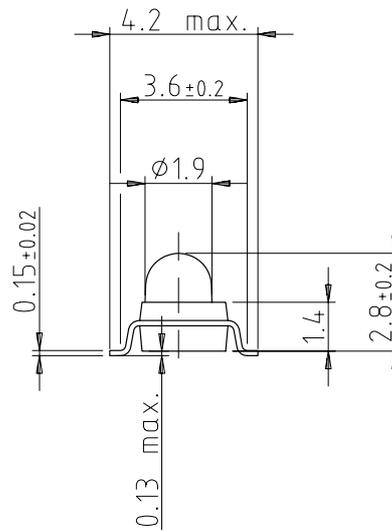


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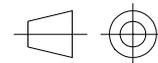


technical drawings according to DIN specifications

Dimensions in mm of TSMF1020

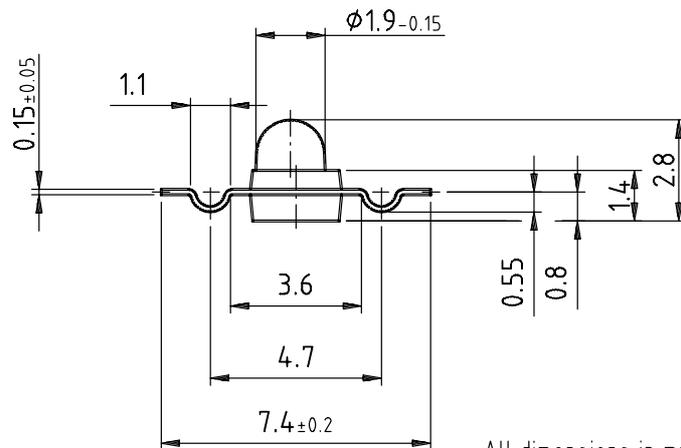


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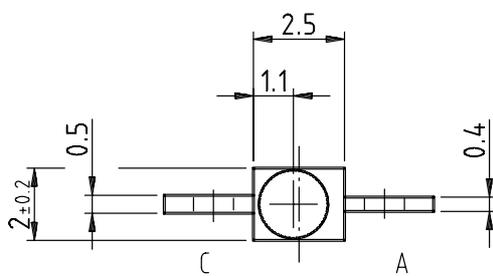


technical drawings
according to DIN
specifications

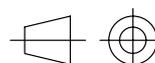
Dimensions in mm of TSMF1030



All dimensions in mm
Not indicated tolerances ± 0.1
Angle $\pm 5^\circ$

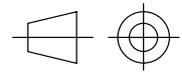
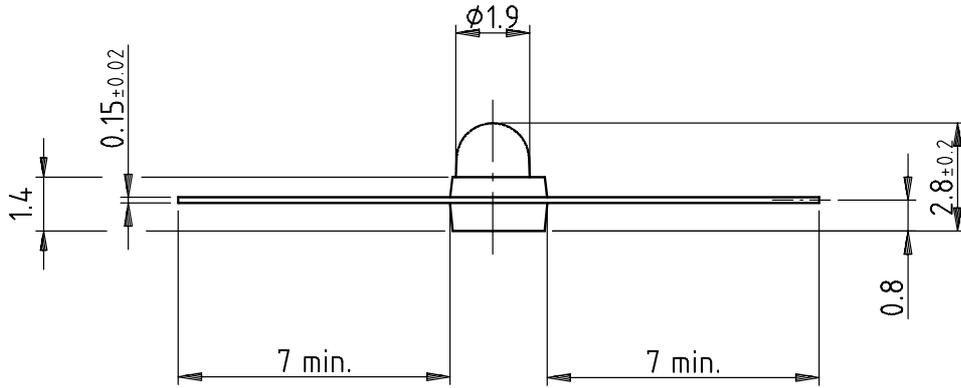


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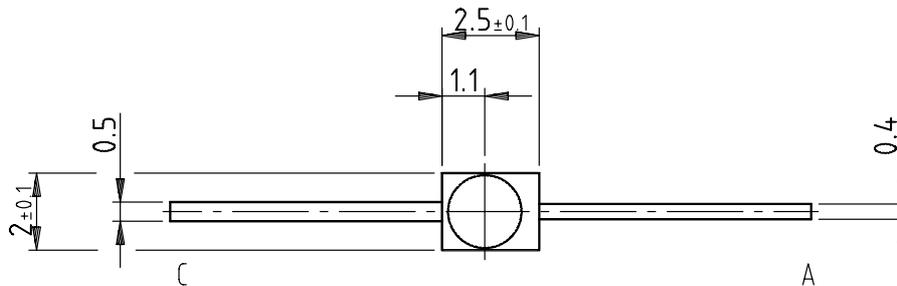
technical drawings
according to DIN
specifications

Dimensions in mm of TSMF1040



technical drawings
according to DIN
specifications

16760





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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